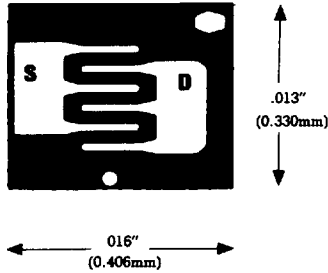


PRODUCT CATALOG

P-CHANNEL JUNCTION FET

CHIP NUMBER

FP22.2



Die Size: 13 x 16 (mils)
0.330 x 0.406(mm)
4 x 6 (mils)
Pad Size: 0.102 x 0.152(mm)
GATE-SUBSTRATE

CONTACT METALLIZATION

Top Contact: > 12,000
Å Aluminum
Backside Contact: 3,000 Å Gold

ASSEMBLY RECOMMENDATIONS

It is advisable that:

- the die be eutectically mounted with gold silicon preform 98/2%.
- 1 mil (0.0254mm) aluminum wire be ultrasonically attached to the top contact.

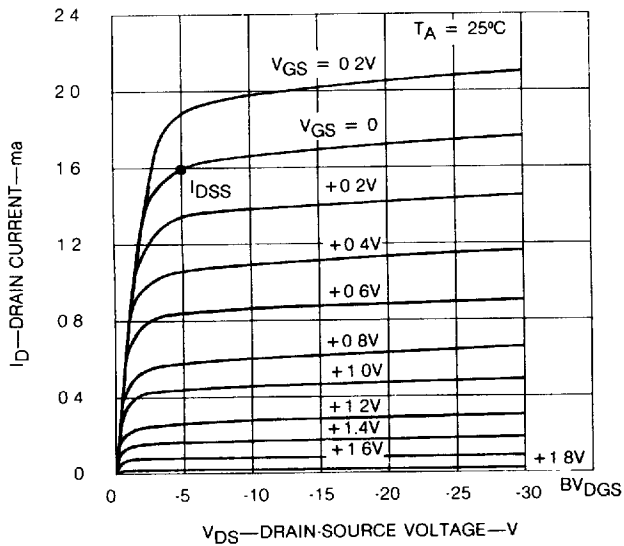
TYPICAL ELECTRICAL CHARACTERISTICS

PARAMETER	MIN.	TYP	MAX.	UNIT	TEST CONDITIONS
BVGSS	40	55		V	$V_{DS} = 0, I_G = 1\mu A$
I_{DSS}	0.1		6	mA	$V_{DS} = -15V, V_{GS} = 0$
V_p	0.5		6	V	$V_{DS} = -15V, I_D = 1nA$
I_{GSS}		20	100	pA	$V_{DS} = 0, V_{GS} = 30V$
G_m	0.2	1	2	mS	$V_{DS} = -15V, V_{GS} = 0, f = 1KHz$
C_{iss}		4	5	pF	$V_{DS} = -15, V_{GS} = 0, f = 1MHz$
C_{rss}		0.9	1.5	pF	$V_{DS} = -15V, V_{GS} = 0, f = 1MHz$

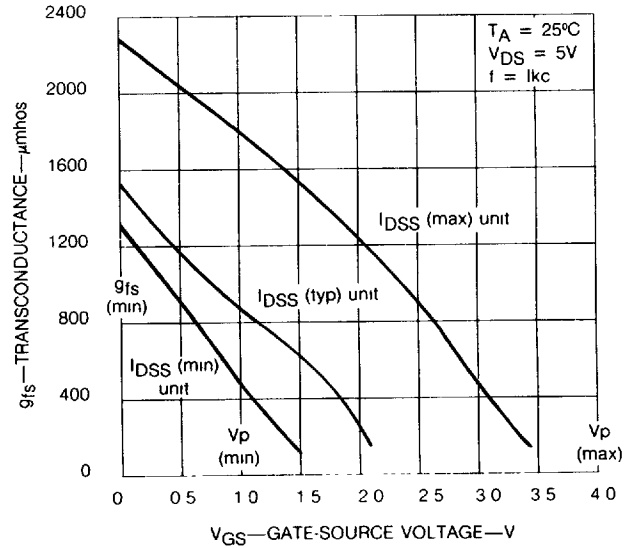
TYPICAL DEVICE TYPES: 2N2606 - 2N2608, 2N3376, 2N3378, 2N3695 - 2N3698

CHIP TYPE FP22..2

TYPICAL OUTPUT CHARACTERISTICS



TRANSCONDUCTANCE vs GATE-SOURCE VOLTAGE



TYPICAL TRANSFER CHARACTERISTICS WITH TEMPERATURE

